

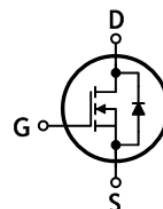
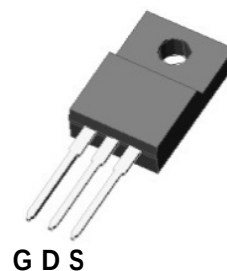
SWITCHING REGULATOR APPLICATION

Features

- Drain-source breakdown voltage: $BV_{DSS}=800V$ (Min.)
- Low gate charge: $Q_g=14.2nC$ (Typ.)
- Low drain-source On resistance: $R_{DS(on)}=3.5\Omega$ (Typ.)
- RoHS compliant device
- 100% avalanche tested

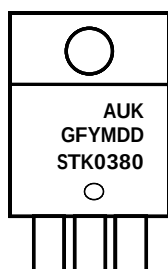
Ordering Information

Part Number	Marking	Package
STK0380F	STK0380	TO-220F-3L



TO-220F-3L

Marking Information



Column 1 : Manufacturer
 Column 2 : Production Information
 e.g.) GFYMDD
 -. G : Option Code (H : Halogen Free)
 -. F : Factory Management Code
 -. YMDD : Date Code (Year, Month, Date)
 Column 3 : Device Code

Absolute maximum ratings ($T_c=25^\circ C$ unless otherwise noted)

Characteristic	Symbol		Rating	Unit
Drain-source voltage	V _{DSS}		800	V
Gate-source voltage	V _{GSS}		±30	V
Drain current (DC) *	I _D	T _c =25°C	3	A
		T _c =100°C	1.8	A
Drain current (Pulsed) *	I _{DM}		12	A
Single pulsed avalanche energy ^(Note 2)	E _{AS}		335	mJ
Repetitive avalanche current ^(Note 1)	I _{AR}		3	A
Repetitive avalanche energy ^(Note 1)	E _{AR}		11.5	mJ
Power dissipation	P _D		30	W
Junction temperature	T _J		150	°C
Storage temperature range	T _{stg}		-55~150	°C

* Limited only maximum junction temperature

Thermal Characteristics

Characteristic	Symbol	Rating	Unit
Thermal resistance, junction to case	$R_{th(j-c)}$	Max. 4.16	°C/W
Thermal resistance, junction to ambient	$R_{th(j-a)}$	Max. 62.5	

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0$	800	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$I_D=250\mu\text{A}$, $V_{DS}=V_{GS}$	3	-	5	V
Drain-source cut-off current	I_{DSS}	$V_{DS}=800\text{V}$, $V_{GS}=0\text{V}$	-	-	1	μA
Gate leakage current	I_{GSS}	$V_{DS}=0\text{V}$, $V_{GS}=\pm 30\text{V}$	-	-	± 100	nA
Drain-source on-resistance (Note 3)	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=1.5\text{A}$	-	3.5	4.5	Ω
Forward transfer conductance (Note 3)	g_{fs}	$V_{DS}=50\text{V}$, $I_D=1.5\text{A}$	-	2.5	-	S
Input capacitance	C_{iss}	$V_{DS}=25\text{V}$, $V_{GS}=0\text{V}$, $f=1.0\text{MHz}$	-	706	917	pF
Output capacitance	C_{oss}		-	54	70	
Reverse transfer capacitance	C_{rss}		-	3.9	7.2	
Turn-on delay time (Note 3,4)	$t_{d(on)}$	$V_{DD}=400\text{V}$, $I_D=3\text{A}$ $R_G=25\Omega$	-	16	42	ns
Rise time (Note 3,4)	t_r		-	44	98	
Turn-off delay time (Note 3,4)	$t_{d(off)}$		-	22	56	
Fall time (Note 3,4)	t_f		-	32	76	
Total gate charge (Note 3,4)	Q_g	$V_{DS}=640\text{V}$, $V_{GS}=10\text{V}$ $I_D=3\text{A}$	-	14.2	-	nC
Gate-source charge (Note 3,4)	Q_{gs}		-	3.4	-	
Gate-drain charge (Note 3,4)	Q_{gd}		-	5.4	-	

Source-Drain Diode Ratings and Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Source current (DC)	I_S	Integral reverse diode in the MOSFET	-	-	3	A
Source current (Pulsed)	I_{SM}		-	-	12	A
Forward voltage	V_{SD}	$V_{GS}=0\text{V}$, $I_S=3\text{A}$	-	-	1.4	V
Reverse recovery time (Note 3,4)	t_{rr}	$I_S=3\text{A}$, $V_{GS}=0\text{V}$ $dI_F/dt=100\text{A}/\mu\text{s}$	-	520	-	ns
Reverse recovery charge (Note 3,4)	Q_{rr}		-	3.2	-	μC

Note:

1. Repeated rating: Pulse width limited by safe operating area
2. $L=69.7\text{mH}$, $I_{AS}=3\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J=25^{\circ}\text{C}$
3. Pulse test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
4. Essentially independent of operating temperature typical characteristics

Electrical Characteristic Curves

Fig. 1 $I_D - V_{DS}$

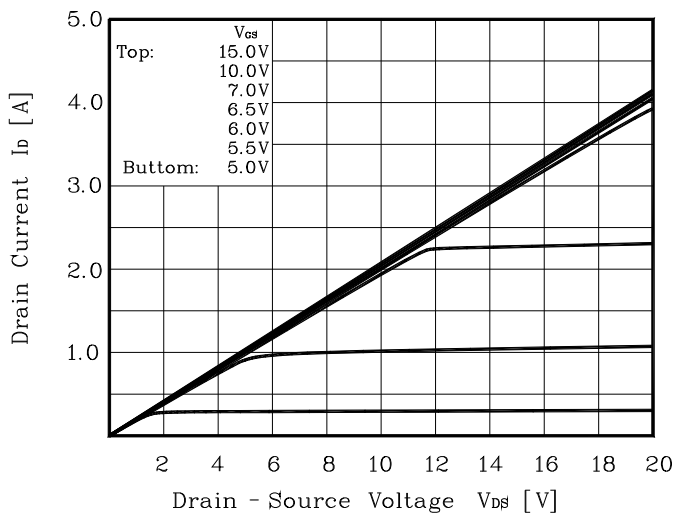


Fig. 2 $I_D - V_{GS}$

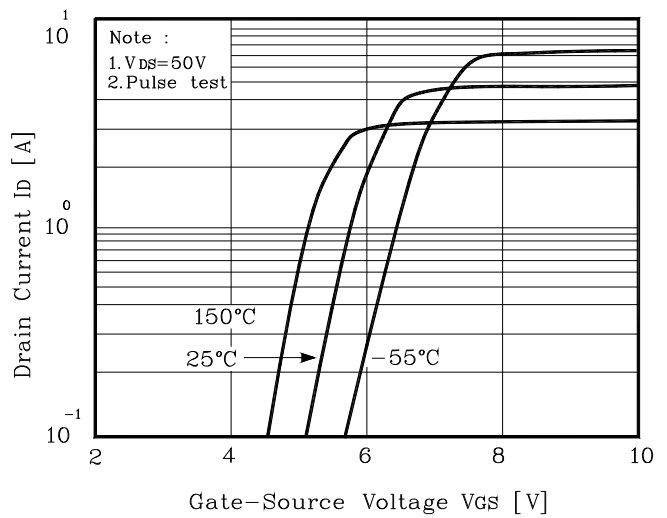


Fig. 3 $R_{DS(on)} - I_D$

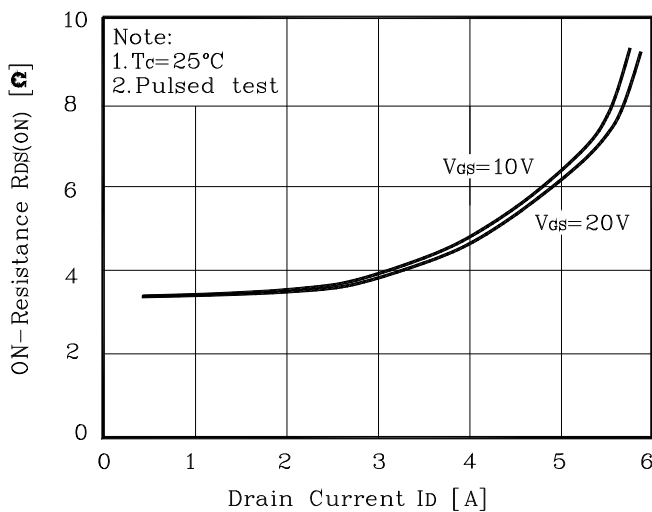


Fig. 4 $I_S - V_{SD}$

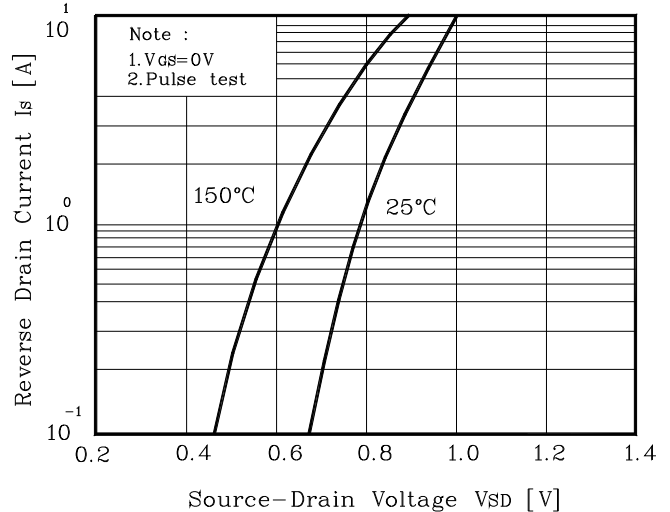


Fig. 5 Capacitance - V_{DS}

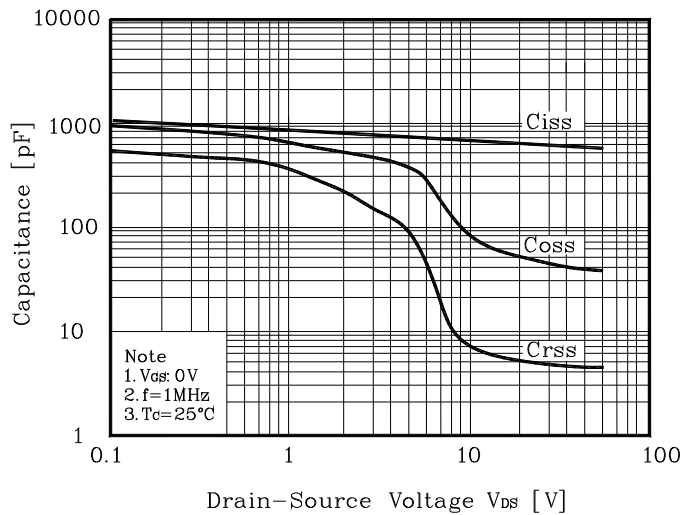
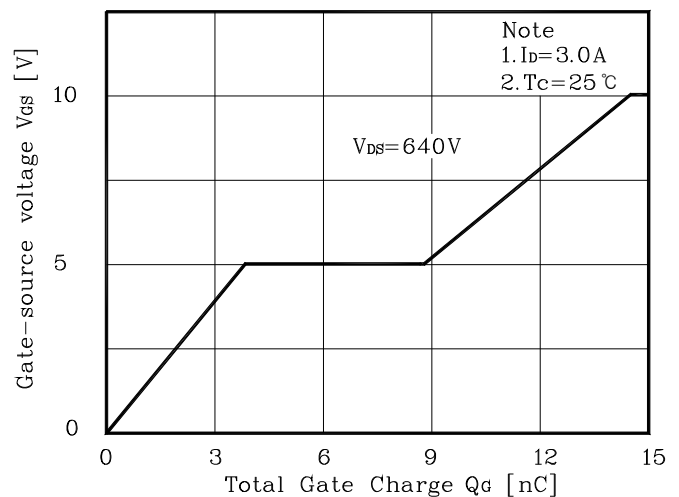


Fig. 6 $V_{GS} - Q_G$



Electrical Characteristic Curves (Continue)

Fig. 7 $V_{DS} - T_J$

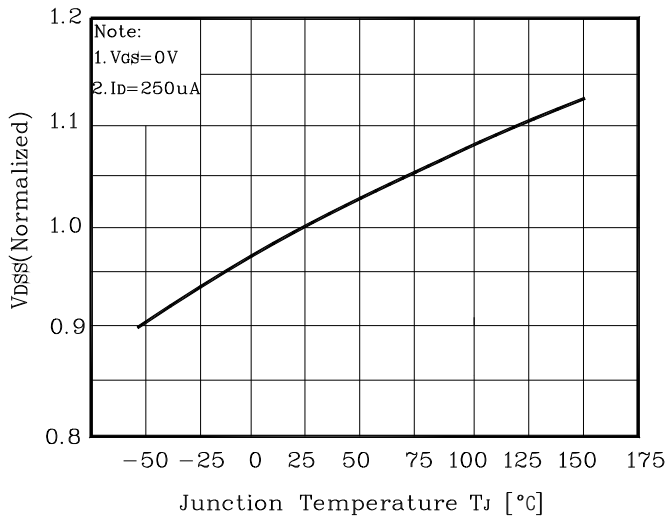


Fig. 8 $R_{DS(on)} - T_J$

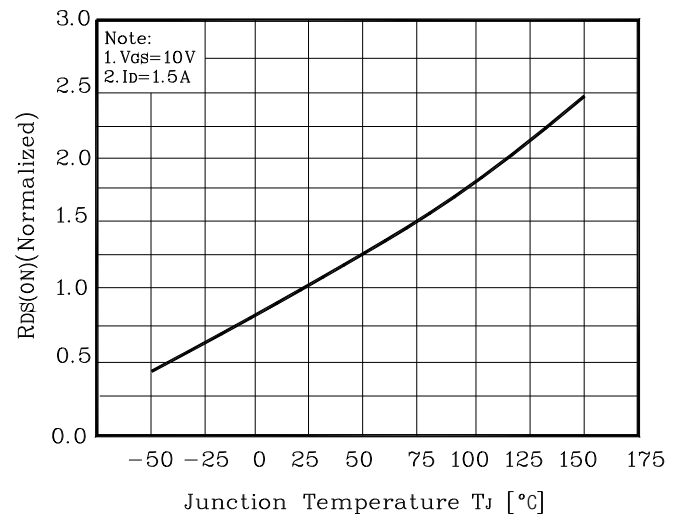


Fig. 9 $I_D - T_C$

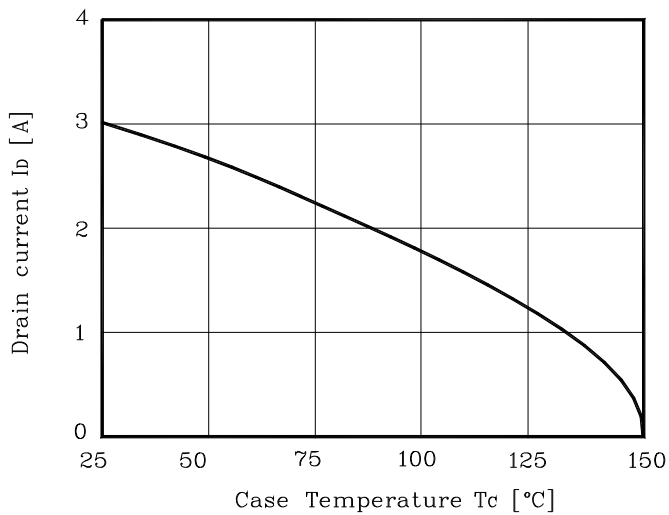


Fig. 10 Safe Operating Area

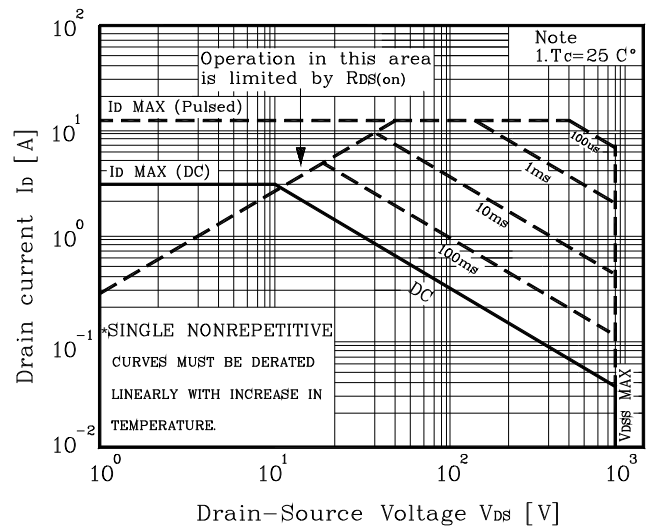


Fig. 11 Gate Charge Test Circuit & Waveform

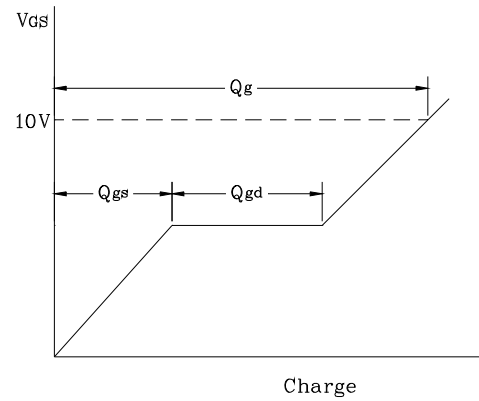
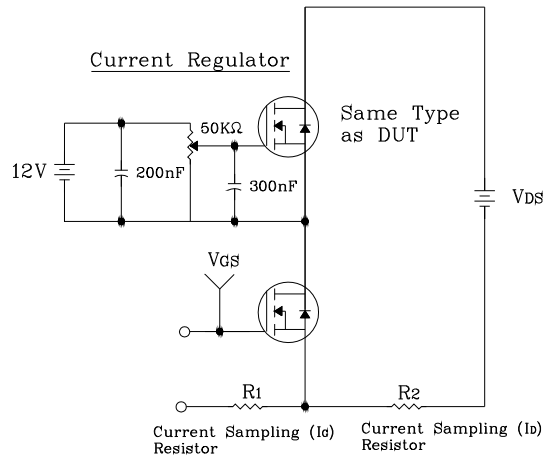


Fig. 12 Resistive Switching Test Circuit & Waveform

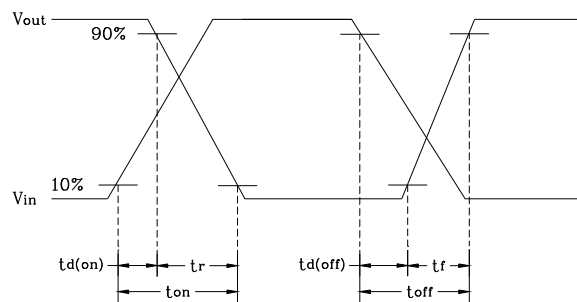
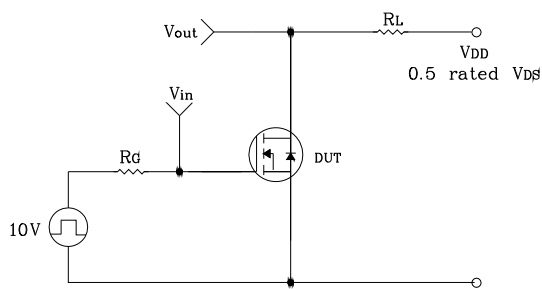


Fig. 13 E_{AS} Test Circuit & Waveform

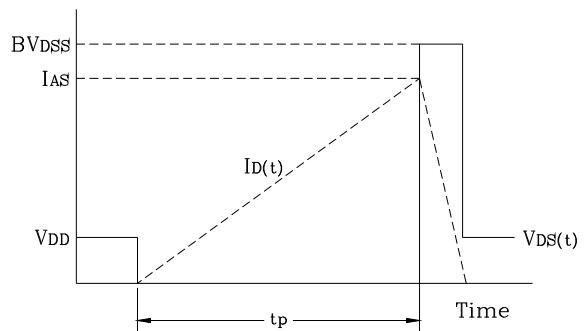
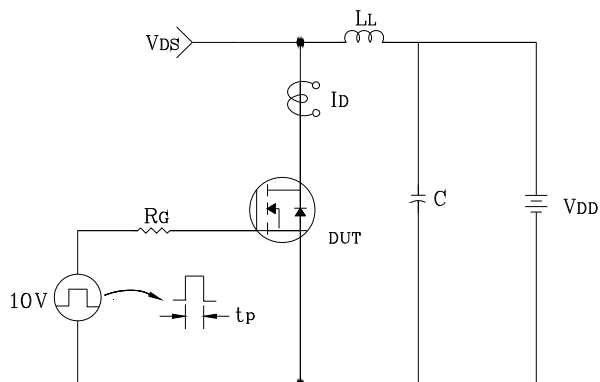
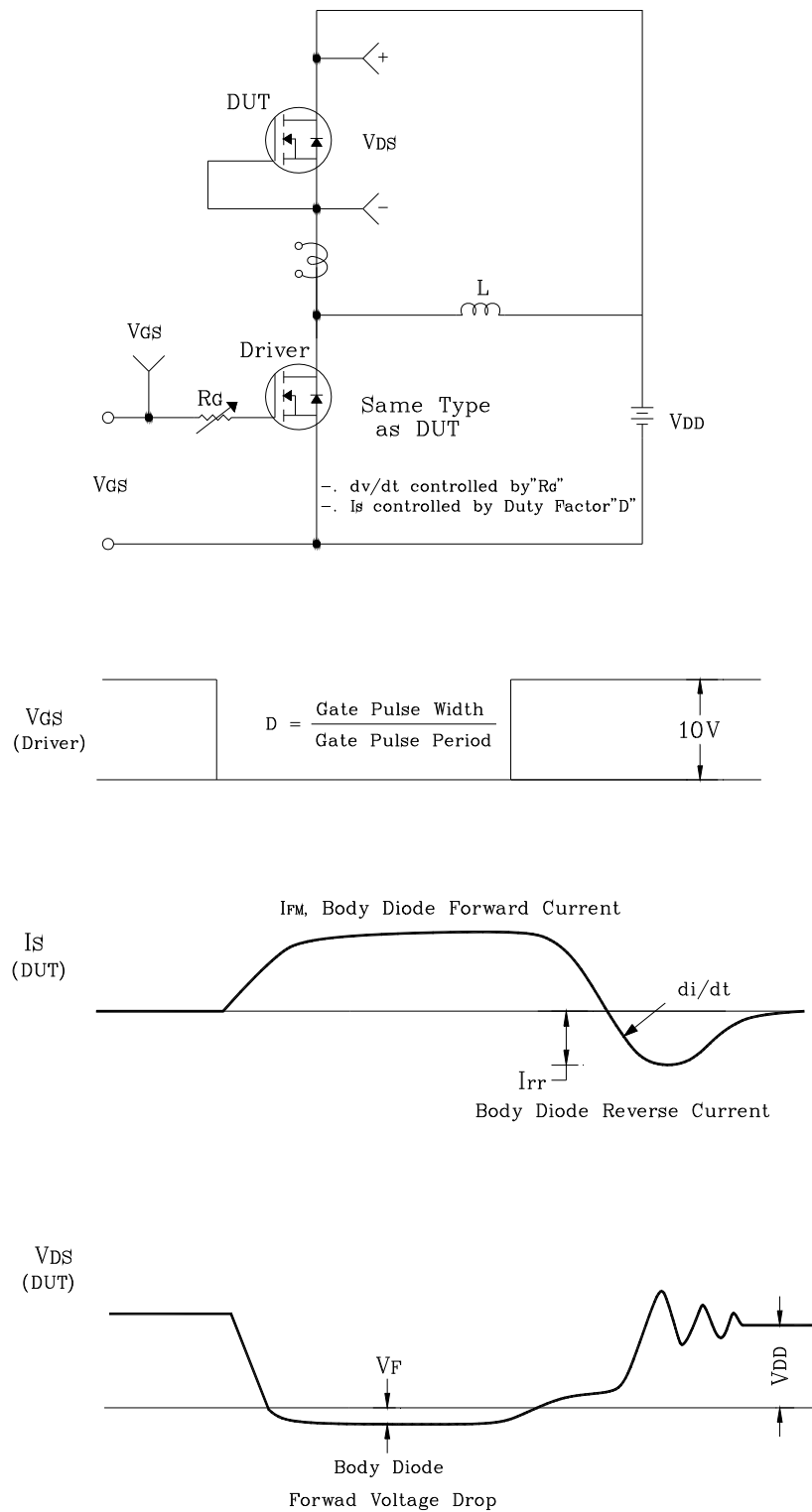
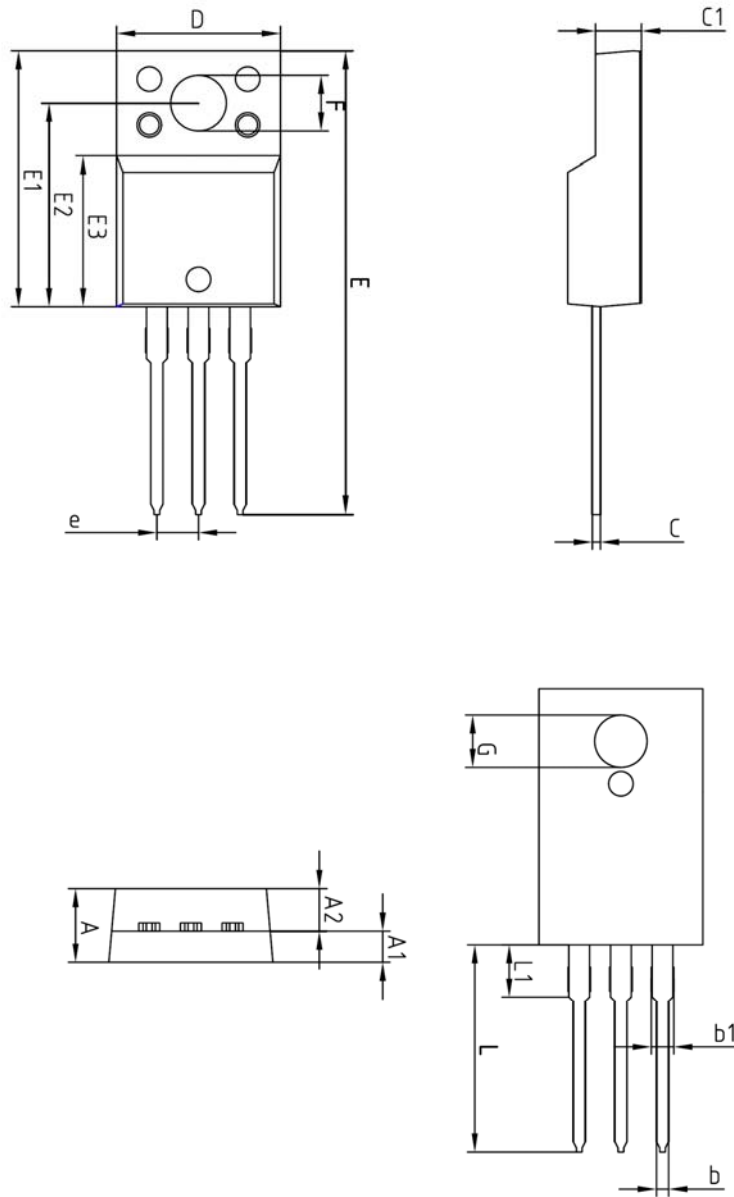


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform



Package Outline Dimensions



SYMBOL	MILLIMETERS			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	—	—	4.60	
A1	2.45	2.50	2.55	
A2	1.95	2.00	2.05	
b	0.65	0.75	0.85	
b1	1.07	1.27	1.47	
C	0.40	0.50	0.60	
C1	2.70	2.80	2.90	
D	9.90	10.00	10.10	
E	28.00	—	28.60	
E1	15.50	15.60	15.70	
E2	12.30	12.40	12.50	
E3	9.15	9.20	9.25	
F	3.30	3.40	3.50	
G	3.10	3.20	3.30	
e	2.54 BSC			
L	12.40	—	13.00	
L1	3.46 BSC			

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